

## Band Switching Diodes - Dual, Series in SOT-323

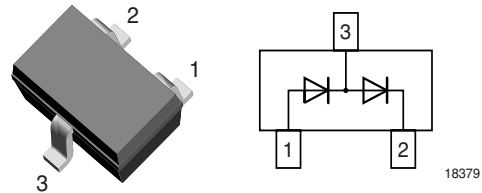
### Description

The main purpose of the BA892V-04W is the Band Switching. Biased with a DC forward current for signals at frequencies over 100 MHz up to 3 GHz this diode behaves like a current controlled resistor and not as a diode any more.

Depending on the forward current the forward resistance  $r_f$  can be switched far below  $1 \Omega$ , so that the Switch is closed.

To open the Switch, the BA892V-04W has to be driven in the reverse mode where the BA892V-04W behaves like a small capacitor with high isolation.

So typical applications for this Band Switching Diode are mobile and TV-applications.



### Features

- Low forward resistance
- Small reverse capacitance

### Applications

Band switching up to 3 GHz  
Low loss band-switching in TV/VTR tuners

### Mechanical Data

**Case:** Plastic case (SOT-323)

**Weight:** approx. 6.0 mg

**Packaging Codes/Options:**

GS08 / 3 k per 7" reel (8 mm tape), 3 k/box

### Parts Table

Part	Ordering code	Marking	Remarks
BA892V-04W	BA892V-04W-GS08	AW4	Tape and Reel

### Absolute Maximum Ratings

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		$V_R$	35	V
Forward current		$I_F$	100	mA
Junction temperature		$T_j$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction soldering point		$R_{thJS}$	100	K/W

### Electrical Characteristics

T<sub>amb</sub> = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Reverse voltage	I <sub>R</sub> = 10 μA	V <sub>R</sub>	35			V
Reverse current	V <sub>R</sub> = 20 V	I <sub>R</sub>			20	nA
Forward voltage	I <sub>F</sub> = 100 mA	V <sub>F</sub>			1.1	V
Diode capacitance	f = 1 MHz, V <sub>R</sub> = 0	C <sub>D</sub>		1.1		pF
	f = 1 MHz, V <sub>R</sub> = 1 V	C <sub>D</sub>		0.9	1.2	pF
	f = 1 MHz, V <sub>R</sub> = 3 V	C <sub>D</sub>		0.85	1.1	pF
Forward resistance	f = 100 MHz, I <sub>F</sub> = 1 mA	r <sub>f</sub>		0.6		Ω
	f = 100 MHz, I <sub>F</sub> = 3 mA	r <sub>f</sub>		0.45	0.7	Ω
	f = 100 MHz, I <sub>F</sub> = 10 mA	r <sub>f</sub>		0.34	0.5	Ω
Charge carrier life time	I <sub>F</sub> = 10 mA, I <sub>R</sub> = 6 mA, i <sub>R</sub> = 3 mA	t <sub>rr</sub>		90		ns

### Typical Characteristics (T<sub>amb</sub> = 25 °C unless otherwise specified)

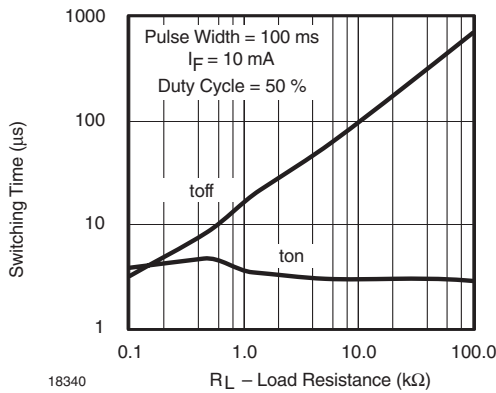


Fig. 1 Forward Resistance vs. Forward Current

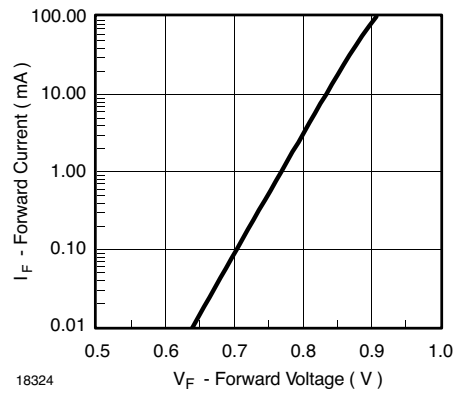


Fig. 3 Forward Current vs. Forward Voltage

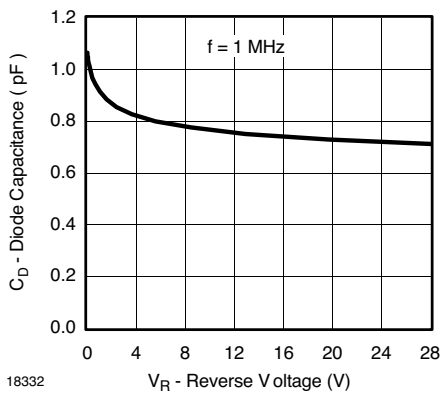


Fig. 2 Diode Capacitance vs. Reverse Voltage

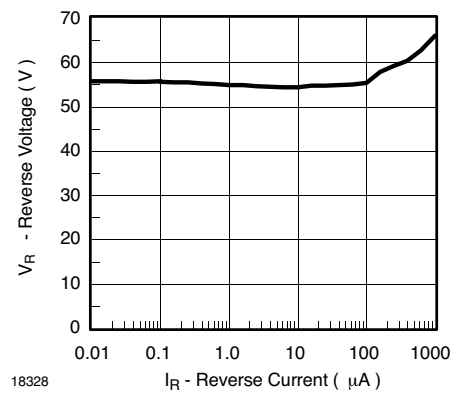


Fig. 4 Reverse Voltage vs. Reverse Current

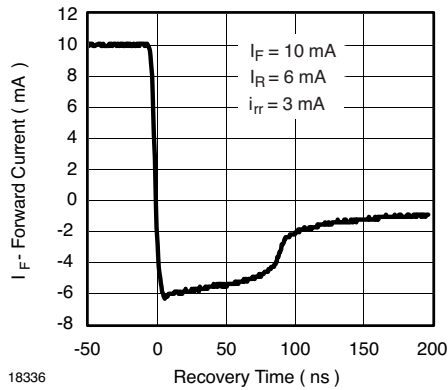
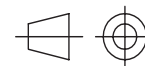
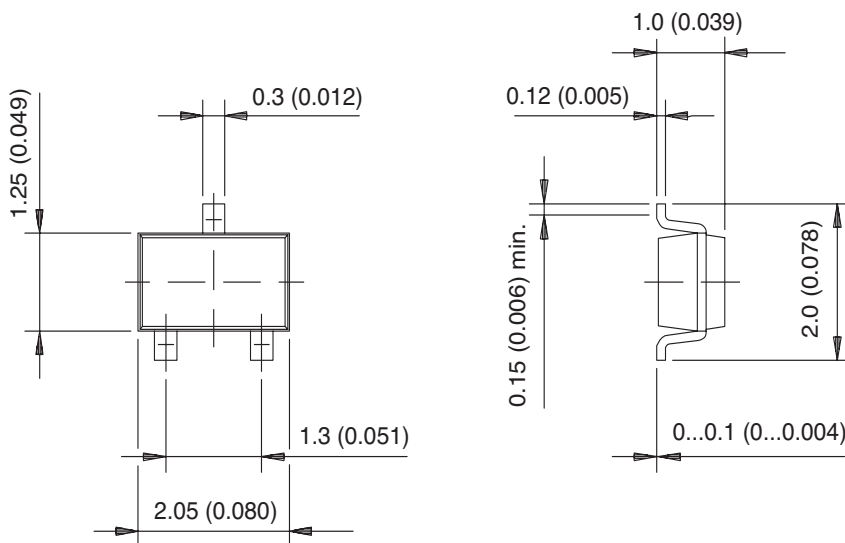


Fig. 5 Typical Charge Recovery Curve

## Package Dimensions in mm



technical drawings  
according to DIN  
specifications

96 12236

### Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design  
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany  
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423